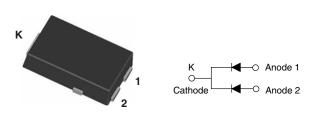
Vishay Semiconductors



Hyperfast Rectifier, 2 x 2 A FRED Pt[®]



TO-277A (SMPC)

PRODUCT SUMMARY						
Package	TO-277A (SMPC)					
I _{F(AV)}	2 x 2 A					
V _R	200 V					
V _F at I _F	0.75 V					
t _{rr (typ.)}	24 ns					
T _J max.	175 °C					
Diode variation	Dual die					

FEATURES

- Hyperfast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- Specific for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage		V _{RRM}		200	V		
Average rectified forward current	per device	I _{F(AV)}	T _{Sp} = 165 °C	4			
Average rectined forward current	per diode			2	A		
Non ropotitivo poek auroa auroat	per device	I _{FSM}	T _J = 25 °C	90			
Non-repetitive peak surge current	per diode			50			
Operating junction and storage temperatures		T _J , T _{Stg}		-65 to +175	°C		

ELECTRICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-		
Forward voltage, par diade	V _F	I _F = 2 A	-	0.88	0.95	V	
Forward voltage, per diode		I _F = 2 A, T _J = 125 °C	-	0.75	0.82		
Poverse leakage autrent par diada	۱ _R	$V_{R} = V_{R}$ rated	-	-	2		
Reverse leakage current, per diode		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	1	8	μΑ	
Junction capacitance	CT	V _R = 200 V	-	8	-	pF	

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RoHS

COMPLIANT

HALOGEN

FREE



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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	24	-			
Povoroo rocovor timo	+	I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A		-	-	25			
Reverse recovery time	t _{rr}	T _J = 25 °C		-	16	-	A nC		
		T _J = 125 °C	I _F = 2 A dI _F /dt = 200 A/μs V _R = 160 V	-	22	-			
Deals recovery ourrent	I _{RRM}	T _J = 25 °C		-	2	-			
Peak recovery current		T _J = 125 °C		-	3	-			
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	16	-			
		T _J = 125 °C		-	30	-			

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C	
Thermal resistance, junction to solder pad, per diode	R _{thJ-Sp}		-	4.5	5.5	°C/W	
Approximate weight				0.1		g	
				0.0035		oz.	
Marking device		Case style TO-277A (SMPC)		JC	H2		

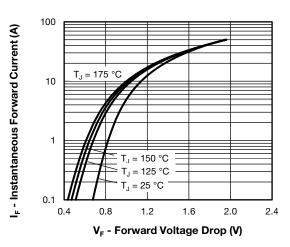


Fig. 1 - Typical Forward Voltage Drop Characteristics

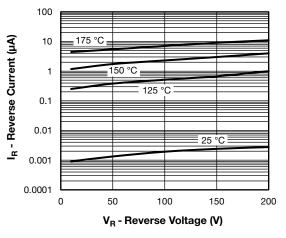
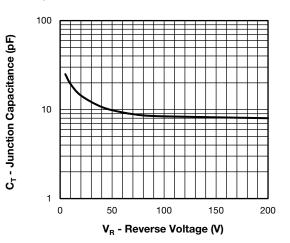


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

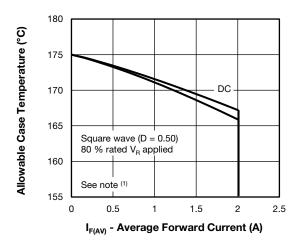


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

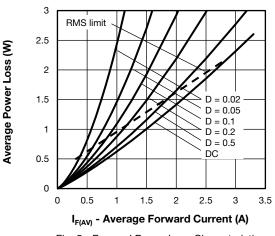


Fig. 5 - Forward Power Loss Characteristics

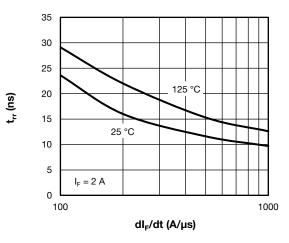


Fig. 6 - Typical Reverse Recovery Time vs. dl_F/dt

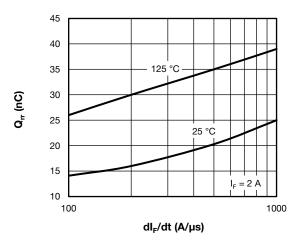


Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{5}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

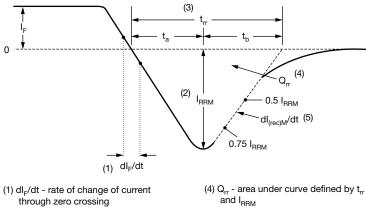
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VS-4CSH02-M3

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(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

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Device coo

е	vs-		4	с	S	н	02	-M3	
			2	3	4	5	6	7	
	1	- Vishay Semiconductors product							
	2	- Current rating (4 = 4 A)							
	3	-	Circ	Circuit configuration:					
			C =	C = common cathode					
	4	-	S =	S = SMPC package					
	5	-	Pro	Process type,					
			H =	H = hyperfast recovery					
	6	-	Volt	Voltage code (02 = 200 V)					
	7	-	-M3	= halog	jen-free	, RoHS-	complia	ant, and	

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-4CSH02-M3/86A	1500	1500	7" diameter plastic tape and reel				
VS-4CSH02-M3/87A	6500	6500	13" diameter plastic tape and reel				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95570				
Part marking information	www.vishay.com/doc?95565				
Packaging information	www.vishay.com/doc?88869				

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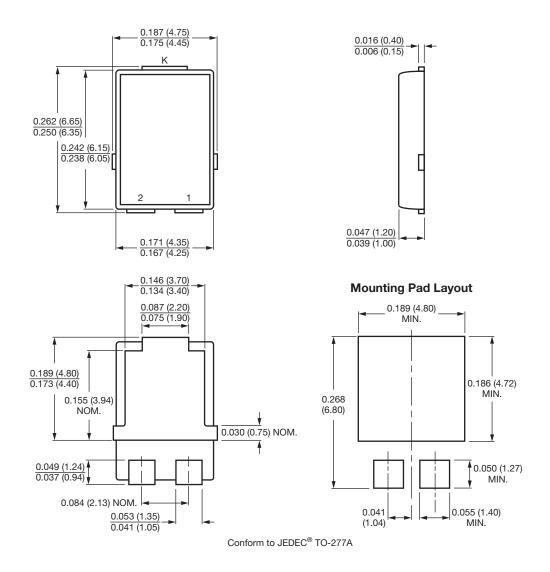
Outline Dimensions





TO-277A (SMPC)

DIMENSIONS in inches (millimeters)





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